R estricted and unrestricted H artree-Fock calculations of conductance for a quantum point contact

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Very short quantum wires (quantum contacts) exhibit a conductance structure at a value of conductance close to 0:7 $2e^2=h$. It is believed that the structure arises due to the electron-electron interaction, and it is also related to electron spin. However details of the mechanism of the structure are not quite clear. Previously we approached the problem within the restricted H artree-Fock approximation. This calculation demonstrated a structure similar to that observed experimentally. In the present work we perform restricted and unrestricted H artree-Fock calculations to analyze the validity of the approximations. We also consider dependence of the electron the electron density in leads. The unrestricted H artree-Fock method allows us to analyze trapping of the single electron within the contact. Such trapping would result in the K ondo model for the $\0.7$ structure". The present calculation con rm s the spin-dependent bound state picture and does not con rm the K ondo model scenario.

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The quantized conductance $G = nG_2$, $n = 1;2;3; :::, G_2 = 2e^2=h$, through a narrow quantum point contact was discovered in 1988^{1;2}. This quantization can be understood within a one-dimensional (1D) non-interacting electron gas picture, see e.g. Ref.³. In the present work we are interested in a deviation from the integer quantization. This deviation, the so called \0.7 structure" has been found in experimental works^{4;5}. The structure is a shoulder-like feature or a narrow plateau at G 0:7G₂. More recent work demonstrates that there are some above barrier excitations related to the structure⁶, and that the structure evolves down to G 0:5G₂ in longer quantum contacts⁷. Dependence of the structure on the longitudinal magnetic eld has been studied already in the pioneering work⁴. This study clearly demonstrated that the ect is somehow related to the electron spin. Authors of a recent experimental work⁸ argue that the structure signals form ation of a K ondo-like correlated spin state.

There have been suggestions to explain the $\0.7$ structure" by spontaneous magnetization of the 1D quantum wire⁹^{{13}</sup>, or by form ation of a two-electron bound state with nonzero total spin^{14;15}. These suggestions in plicitly assume that 2D leads connected to the contact are qualitatively important for the electron because there is the rigorous Lieb-M attis theorem ¹⁶ that claims that the ground state of a 1D m any-body system has zero spin.

A Hatree-Fock calculation of the conductance has been performed in the $Ref.^{17}$. This calculation demonstrated a structure similar to that observed experimentally. The ground state has zero spin in accordance with the Lieb-M attist heorem, but nevertheless the structure found in the calculation is intrinsically related to the spin because it disappears without account of the exchange electron-electron C oulomb interaction. The structure is related to the formation of the charge density wave within the contact or in other words to the spin-dependent bound state within the contact.

The present work has been stimulated by the recent suggestion that the 0.7-structure signals form ation of a K ondo-like correlated spin state⁸, see also R ef.¹⁸. The restricted H artree Fock (RHF) approximation employed in Ref.¹⁷ is not su cient to follow this suggestion. However the unrestricted Hartree-Fock (UHF) approach can shed light on the problem. In the present work we consider only zero tem perature case. The RHF m ethod in plies that spin up and spin down single electron orbitals are identical while in the UHF m ethod those orbitals are com pletely independent. The RHF is explicitly rotationally invariant, but it is not very e ective in accounting for electronelectron correlations. The UHF is much better at accounting for the correlations, but it violates the rotational invariance. There is no doubt that even UHF cannot account for the long range K ondo-like dynam ics. However it can indicate localization of a single electron within the contact. This would immediately imply the Kondo-like dynamics. Our calculation shows that such localization can take place in longer contacts and at low electron density in leads. However it always leads to a very special dependence of conductance on the gate voltage which is dierent from that observed experimentally. In the regime when the dependence of conductance on the gate voltage is similar to the experimental one the results of RHF and UHF are practically identical and this indicates the validity of both approximations. We also study dependence of the 0.7 structure" on the electron density in the leads. The structure disappears at high density and it is getting more pronounced at the low density in a qualitative agreem ent with experim ent.

It is well known, see $Ref.^3$, that in the independent particle approximation, i.e. in the case of an ideal electron gas, the conductance for a given transverse channel is proportional to the barrier transm ission probability at Ferm i energy T,

$$G = \frac{2e^2}{h}T:$$
 (1)

the density of electrons is high enough, and hence the interaction is negligible. However one cannot use a single particle description to calculate the transm ission probability T because in the vicinity of the barrier the electron density is low, and hence the many-body e ects are very in portant. To calculate the transm ission probability T the following method is applied. Consider electrons on a 1D ring of the length L with a potential barrier of the length 1 somewhere on the ring. It is important that L 1. There is no current in the ground state of the system. Now let us apply a magnetic ux through the ring. This ux induces the electric current. Note that it is not a realm agnetic eld, this is a ctitious gauge eld that generates the current without applying any voltage. It is especially convenient to take the gauge eld that provides the Bohm -A haronov phase ' = -2. We use this choice in our calculations. The induced current can be calculated by solving many-body Schroedinger equation. It can be an exact solution or an approximate one like RHF or UHF. It has been demonstrated in Ref.¹⁷ that to not the barrier transm ission probability at Ferm integration gauges the transm ission probability, $T = (J_U = J_0)^2$. This form ula is valid without an external magnetic eld. Repeating considerations of Ref.¹⁷ one can prove that with the magnetic eld, i.e. with the spin splitting, the e ective transm ission probability is given by

$$T = \frac{1}{2}T_{*} + \frac{1}{2}T_{\#}; \quad T = \frac{J_{U}}{J_{0}}^{2}; \qquad (2)$$

where $J_{\#}$ is the electric current of electrons with spin up and spin down correspondingly. Equation (2) can be also applied for UHF calculations without an external magnetic eld. The relation $T = (J_U = J_0)^2$ has been applied recently to study conductance through a system of strongly correlated spinless ferm ions¹⁹. In this work the many-body problem has been treated exactly via the Density M atrix Renorm alization G roup algorithm.

The Ham iltonian of the many body system we consider is of the form

$$H = \frac{X}{i} \frac{(p_{i} A)^{2}}{2} + U(x_{i}) + \frac{1}{2} \frac{X}{i_{j}} V(x_{i};x_{j});$$
(3)

where indexes i and j num erate electrons, x_i is the periodic coordinate on the ring of length L (0 < x < L), and A = = 2L is the ctitious gauge eld. The electron-electron C oulom b repulsion is of the form

$$V(x;y) = \frac{1}{a_{t}^{2} + D^{2}(x;y)};$$
(4)

where $a_t = 2$ is the electric width of the transverse channel, see Ref.⁷, and D (x;y) is the length of the shortest arc between the points x and y on the ring. We use atom ic units, so distances are measured in units of B ohr radius, $a_B = h^2 = m e^2$, and energies are measured in units of $E_{unit} = m e^4 = h^2 e^2$, where m is the electric mass and is the dielectric constant. For experimental conditions of works⁴⁸ these values are the following: $a_B = 10^2 m$, $E_{unit} = 10^2 eV$. To model the gate potential we use the following form ula for the potential barrier

$$U(\mathbf{x}) = \frac{U_0}{e^{(\mathbf{x}) \pm 2} = d + 1}; \quad d = \pm 10:$$
(5)

Plots of U (x) for \models 8,10,12 are shown in Fig.1.

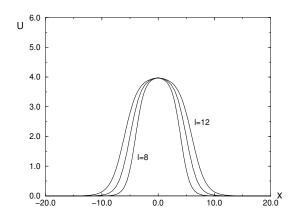


FIG.1. The "gate" potential (5) at $U_0 = 4$ and l = 8;10;12.

To solve the many-body problem described by the Ham iltonian (3) we use the Hartree-Fock (HF) approximation. In the HF approximation the many body wave function is represented in the form of the Slater determinant of single particle orbitals $'_{i}$ (x). The index is shows the coordinate state of the orbital, and the index = 1=2 shows the spin state of the orbital. Each orbital obeys the equation

$$\hat{\mathbf{h}'}_{\mathbf{i}} = \mathbf{i}'_{\mathbf{i}}; \tag{6}$$

where i is the single particle energy and \hat{h} is the HF H am iltonian

$$\hat{h}'_{i}(x) = \frac{(p - A)^{2}}{2} + U_{eff}(x) '_{i}(x) '_{j}(y)'_{i}(y)V(x;y)dy'_{j}(x);$$

$$U_{eff} = U(x) + \frac{X}{j} J_{j}(y)^{2}V(x;y)dy:$$
(7)

The sum mations are performed over all led orbitals. In the Restricted Hartree-Fock (RHF) method an additional constraint, $'_{i"}(x) = '_{i\#}(x)$, is imposed on the solutions of Eqs. (7). This provides rotational invariance of the solution. In the Unrestricted Hartree-Fock method (UHF) the additional constraint is om itted. As a result the UHF method provides much better account of electronic correlations. The price for this is a spontaneous violation of the rotational invariance.

For computations we use a nite grid. In the grid modi cation of the H am iltonian (7) the kinetic energy $(p A)^2'$ is replaced by $2j'(n)j'' (n+1)e^{iAh'}(n) '(n)e^{iAh'}(n+1) = 2h^2$. Here h is the spacing of the grid and '(n) is the wave function on site n of the grid. The electric current corresponding to the grid H am iltonian reads

$$J = \int_{j}^{X} \frac{i}{2h} \prime_{j} (n) e^{iAh} \prime_{j} (n+1) \prime_{j} (n+1) e^{iAh} \prime_{j} (n) :$$
(8)

The current is conserved because of the gauge invariance of HF equations.

For computations we use a grid of 400 points on a ring of length L = 80. Total z-projection of the spin is zero, so the number of electrons with spin up is equal to that with spin down, N " = N $_{\#}$. We perform calculations for the total number of electrons N = N $_{\#}$ + N $_{\#}$ = 78;118;158. This corresponds to the following values of the number density of electrons on the ring: $n_0 = N = L$ 1;1:5;2. This is the electron linear density, therefore one cannot compare n_0 quantitatively with the density of electrons in real two-dimensional leads used in experiments⁴^{{8}</sup>. However a qualitative comparison is possible: the smaller the real density, the smaller n_0 , and hence the smaller the C oulom b screening. Results of calculations for three di erent values of the barrier length, l = 8, l = 10, l = 12, and three di erent values of the electron density in the \leads", n_0 1, n_0 1:5, and n_0 2, are shown in F ig 2. The transm ission probability T is plotted versus the gate potential U₀. Solid lines correspond to the RHF approximation.

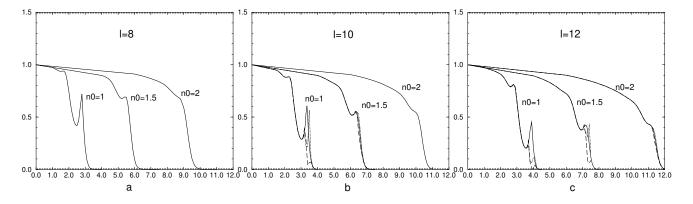


FIG.2. Plots of the transmission probability T versus the gate potential U_0 for three dimension values of the barrier length, l=8, l=10, l=12, and for three dimension values of the electron density in the \leads", $n_0 = 1, n_0 = 1.5$, and $n_0 = 2$. Solid lines show results of RHF calculations while dotted and dashed lines show spin up (T_{*}) and spin down (T_#) transmission probabilities calculated within the UHF m ethod. D otted and dashed lines in Fig."a" (l= 8) are not distinguishable from solid ones.

The RHF calculation for n_0 2 has been performed earlier in Ref.⁷. All the plots presented in Fig.2 clearly demonstrate structures of the conductance. An important point is that reduction of the electron density in leads and hence reduction of screening results in enhancement of the structure. Another feature is the evolution of the

structure down for longer contacts. The results of UHF calculations are shown in the same Fig.1 by dotted and dashed lines. The dotted line shows the transm ission probability for the spin \u00d1p" channel and the dashed line shows the same for the spin \down" channel. Certainly the choice of \u0" and \down" is arbitrary, one can swap the spins. The UHF method always gives two degenerate solutions. For l = 8 the UHF results are not presented because they are hardly distinguishable from that of the RHF method shown by solid lines. A coording to Eq. (2) the observable transm ission coe cient is the average of T * and T*. The results of RHF and UHF methods are very close. To demonstrate the closeness we also present in Fig.3 plots of electron densities n* (x) and n* (x) for parameters (U_0 = 6:1, n_0 = 1:5) and (U_0 = 6:4, n_0 = 1:5) that correspond to two points on the shoulder in Fig.2b. Solid lines represent the RHF density, n* (x) = n* (x). The dotted line and the dashed line represent UHF densities n* (x) and n* (x) correspondingly. In case (a) (U_0 = 6:4, n_0 = 1:5) they are distinguishable, but very close.

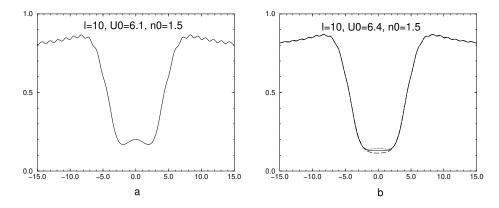


FIG.3. Electron densities $n_*(x)$ and $n_{\#}(x)$ for parameters ($U_0 = 6:1, n_0 = 1:5$) and ($U_0 = 6:4, n_0 = 1:5$) that correspond to two points on the shoulder in Fig.2b. The solid lines show RHF density, $n_*(x) = n_{\#}(x)$. The dotted line and the dashed line show UHF densities $n_*(x)$ and $n_{\#}(x)$ correspondingly. In the case (a), ($U_0 = 6:1, n_0 = 1:5$), the dotted and the dashed lines are not distinguishable from the solid one.

A coording to Fig 2 the RHF and UHF m ethods really disagree only at l = 12, $n_0 = 1$, $U_0 > 3$:7: relatively long contact, very low electron density in leads, and small conductance. This is the regime where the K ondo m odel is relevant. To understand what is going on in this situation we present in Fig A plots of electron densities $n_*(x)$ and $n_*(x)$ at $U_0 = 4$. As in the above gures, the solid line represents the RHF calculation, and dotted and dashed lines represent the UHF calculation.

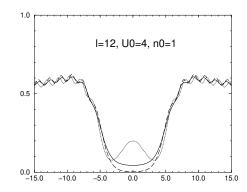


FIG.4. Electron densities for parameters l = 12, $n_0 = 1$, and $U_0 = 4$ that correspond to the structure in the left curve in Fig.2c. The solid line shows the RHF density, $n_*(x) = n_{\#}(x)$. The dotted line and the dashed line show UHF densities $n_*(x)$ and $n_{\#}(x)$ correspondingly.

C learly in this situation the RHF approximation is wrong. A coording to the UHF calculation the spin down electron density within the contact is practically zero and, on the other hand, there is one spin up electron localized in the contact. There is no doubt that in this case dynamics of the contact is K ondo-like. In this case even the UHF m ethod does not give a correct transm ission coe cient because the m ethod does not take into account long-range K ondo dynam ics. However, fortunately, the answer is well known; the transm ission coe cient is peaked up to unity, see Ref.²⁰. So, the correct plot of the transm ission coe cient at l = 12 and $n_0 = 1$ coincides with that presented in Fig.2c for $U_0 < 3.7$, and then there is a narrow peak up to T = 1 at $U_0 = 4$. It is interesting to note that the transm ission coe cients calculated within the Hartree-Fock approximation for $n_0 = 1$ and for shorter contacts (Fig.2a,b) have a qualitatively sim ilar dependence: deep minimum and a narrow peak. This sim ilarity

clearly dem onstrates how the several-electron bound state that can be assessed by the Hartree-Fock m ethod (Fig.2a, $n_0 = 1$) evolves to the multi-electron K ondo bound state that cannot be assessed by this m ethod (Fig.2c, $n_0 = 1$).

It is interesting that for longer contacts one can trap more than one electron in the contact. To illustrate this in Fig.5 we show UHF electron densities $n_{*}(x)$ and $n_{\#}(x)$ for a contact of length l = 20 and density in the leads $n_{0} = 0.56$. In this case the two electron solution of the type shown in Fig.5a is realized at the gate potential $1:3 < U_{0} < 1.85$, then at $1.85 < U_{0} < 2.15$ the solution \jumps" to the single electron state shown in Fig.5a. At the higher gate potential there are no electrons in the contact. So adjusting the length of the contact, the density of electrons in leads, and the gate potential one can pin within the contact a single electron like it is shown in Fig.4 and Fig.5b or even the two electron \modelmodecule" shown in Fig.5a. However, before getting to this very strongly correlated regime the transmission probability dips down to the value of few percent. At most the probability in the dip is 20% as it is shown in Fig.2c ($n_{0} = 1$). There are no such dips in experimental data. Therefore it is unlikely that K ondo dynam ics can be relevant to the electron diverse in works^{4 {8}}. On the other hand the plots shown in Fig.2a, b, c for $n_{0} = 1:5$ and $n_{0} = 2$ look very similar to the experimental data. Structures on these plots are related to the few electron spin dependent bound state. The closest physical analogy in this case is probably the Peierls spin-density instability.

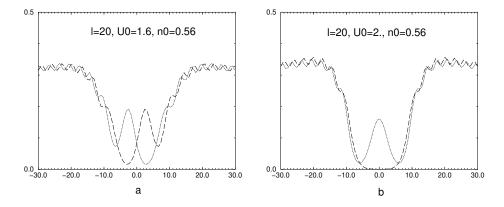


FIG.5. UHF electron densities $n_{*}(x)$ (dotted line) and $n_{*}(x)$ (dashed line) for a \very" long contact, l = 20, and for a \very" low electron density in leads, $n_{0} = 0.56$.

In conclusion, within a one-dimensional model we have analyzed the conductance of a short quantum contact at zero tem perature. Restricted (RHF) and unrestricted (UHF) Hartree-Fock methods have been used in the analysis. Both methods clearly demonstrate structures very similar to that observed in Refs.⁴⁸. A greement between RHF and UHF methods con most be validity of both approximations. The conductance structure is related to the charge density wave developed in the contact. This is a spin dependent elect because without the exchange interaction the structure disappears, so this is a kind of spin-dependent bound state within the contact. Reduction of the electron density in the leads and hence reduction of the screening results in enhancement of the structure. The structure evolves down for longer contacts.

H aving the contact long enough, the density of electrons in the leads low enough, and adjusting the gate potential one can pin within the contact a single electron or even a two electron \m olecule". The single electron would im ply K ondo-like dynam ics as has been suggested in R efs.^{8;18}. However, according to our calculations, before getting to this regime the transm ission probability as a function of the gate voltage dips down to at least 20%. Such dip has never been observed experimentally. Therefore it is unlikely that K ondo dynam ics can be relevant to the electron before getting to observed in works^{4 {8}.

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